

AMENDMENTS TO THE SPECIFICATION

Please amend the Specification as follows. Insertions are shown underlined while deletions are ~~struck through~~.

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[0046] Subsequently, a liquid raw material Cu(hfac)tmvs inside the raw material tank 25 is brought into the inlet port 12 of the valve unit 10 with its flow being controlled at 4g/min. (in other embodiments, 0.5-15g/min.) by the liquid mass flowmeter 26. Being mixed with Ar gas, the liquid raw material in the form of a fine liquid mist is fed from the orifice 2 into the reaction chamber 7. As shown in Fig. 3, the evaporation plate 3 is a hollow plate comprising an upper plate 50 constituting the vaporization surface 30 and a lower plate 51 constituting the bottom surface 31, between which an interior 52 is formed. ¶The liquid raw material fed at room temperature vaporizes while flowing on a vaporization surface 30 of the evaporation plate 3 in the direction of Arrow 42, passes through pores 32 and 33 via the interior 52, and is emitted onto the semiconductor wafer 9 through the fine pores 14 of the shower plate 4. At this time, by the pressure sensors 22 and 23, pressures on the upstream side and on the downstream side of the shower plate 4 are detected. By monitoring the pressures by the pressure monitoring device 27, whether the liquid raw material vaporizes normally or not can be verified. Figs. 4(A) and 4(B) show changes with time of a pressure P1 (detected by the sensor 22) inside the space 6 on the upstream side of the shower plate 4 and of a pressure P2 (detected by the sensor 23) inside the reaction chamber 7 on the downstream side of the shower plate 4 when Ar gas and Cu(hfac)tmvs are fed.